

## N-Channel Super Junction Power MOSFET II

### General Description

The series of devices use advanced super junction technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

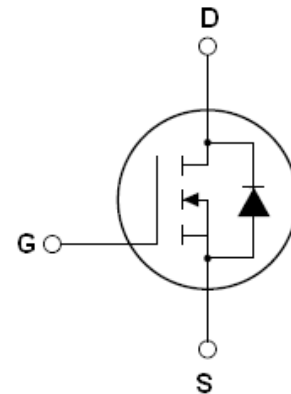
### Features

- New technology for high voltage device
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

### Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

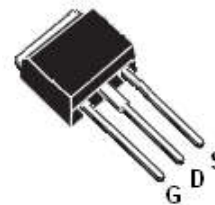
$V_{DS@T_{jmax}}$	710	V
$R_{DS(ON) TYP}$	2.2	$\Omega$
$I_D$	2	A



Schematic diagram

### Package Marking And Ordering Information

Device	Device Package	Marking
TGD65R2K2I	TO-251	TGD65R2K2I
TGD65R2K2K	TO-252	TGD65R2K2K



TO-251



TO-252

Table 1. Absolute Maximum Ratings ( $T_c=25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain-Source Voltage ( $V_{GS}=0V$ )	$V_{DS}$	650	V
Gate-Source Voltage ( $V_{DS}=0V$ )	$V_{GS}$	$\pm 30$	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	2	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	1.3	A
Pulsed drain current (Note 1)	$I_{DM(pluse)}$	6	A
Maximum Power Dissipation( $T_c=25^\circ\text{C}$ )	$P_D$	23	W
Derate above $25^\circ\text{C}$		0.184	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note2)	$E_{AS}$	45	mJ
Avalanche current (Note 1)	$I_{AR}$	1	A
Repetitive Avalanche energy, $t_{AR}$ limited by $T_{jmax}$ (Note 1)	$E_{AR}$	0.06	mJ



Parameter	Symbol	Value	Unit
Drain Source voltage slope, $V_{DS} \leq 480V$ ,	dv/dt	50	V/ns
Reverse diode dv/dt, $V_{DS} \leq 480V, I_{SD} < I_D$	dv/dt	15	V/ns
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55...+150	°C

**Table 2. Thermal Characteristic**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	$R_{thJC}$	5.4	°C /W
Thermal Resistance, Junction-to-Ambient (Maximum)	$R_{thJA}$	75	°C /W

**Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>On/off states</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current( $T_C=25^\circ C$ )	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V$			1	$\mu A$
Zero Gate Voltage Drain Current( $T_C=125^\circ C$ )	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V$			10	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3	3.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=1A$		2200	2500	m $\Omega$
<b>Dynamic Characteristics</b>						
Forward Transconductance	$g_{FS}$	$V_{DS} = 20V, I_D = 1A$		2		S
Input Capacitance	$C_{iss}$	$V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$		190		PF
Output Capacitance	$C_{oss}$			13		PF
Reverse Transfer Capacitance	$C_{rss}$			1.1		PF
Total Gate Charge	$Q_g$	$V_{DS}=480V, I_D=2A,$ $V_{GS}=10V$		3.2	10	nC
Gate-Source Charge	$Q_{gs}$			0.6		nC
Gate-Drain Charge	$Q_{gd}$			1.2		nC
Intrinsic gate resistance	$R_G$	$f = 1 MHz$ open drain		9		$\Omega$
<b>Switching times</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=380V, I_D=1A,$ $R_G=50\Omega, V_{GS}=10V$		6		nS
Turn-on Rise Time	$t_r$			3		nS
Turn-Off Delay Time	$t_{d(off)}$			65		nS
Turn-Off Fall Time	$t_f$			11		nS
<b>Source- Drain Diode Characteristics</b>						
Source-drain current(Body Diode)	$I_{SD}$	$T_C=25^\circ C$			2	A
Pulsed Source-drain current(Body Diode)	$I_{SDM}$				6	A
Forward On Voltage	$V_{SD}$	$T_j=25^\circ C, I_{SD}=2A, V_{GS}=0V$		1	1.3	V
Reverse Recovery Time	$t_{rr}$	$T_j=25^\circ C, I_F=2A, di/dt=100A/\mu s$		140		nS
Reverse Recovery Charge	$Q_{rr}$			0.65		$\mu C$
Peak reverse recovery current	$I_{rrm}$			9		A

Notes: 1.Repetitive Rating: Pulse width limited by maximum junction temperature

2.  $T_j=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

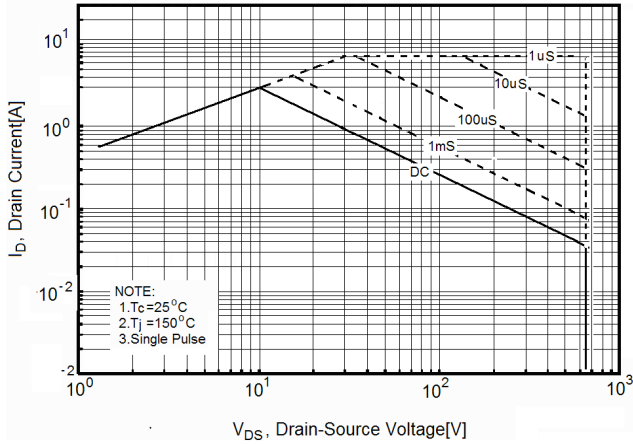


Figure2. Source-Drain Diode Forward Voltage

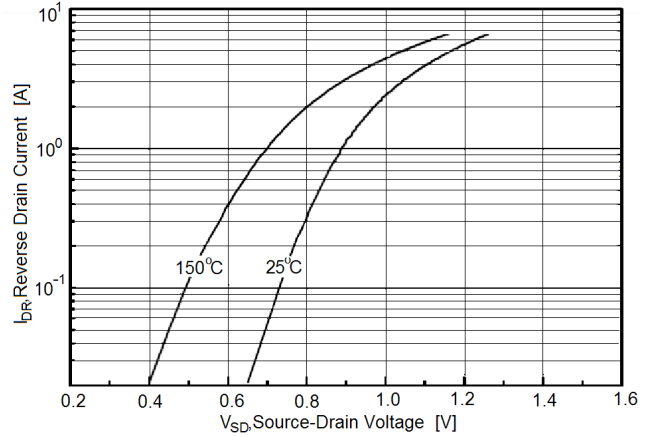


Figure3. Output characteristics

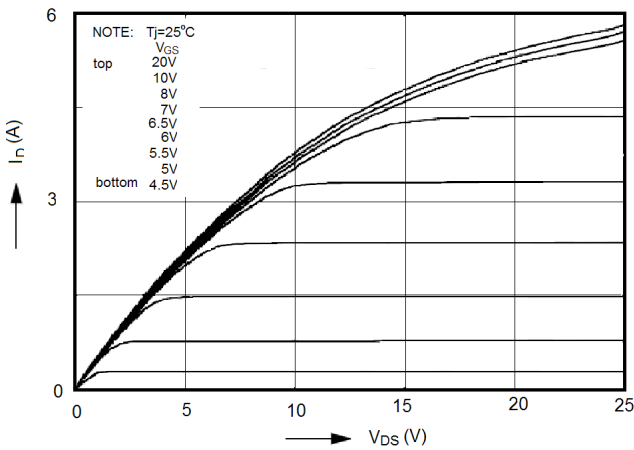


Figure4. Transfer characteristics

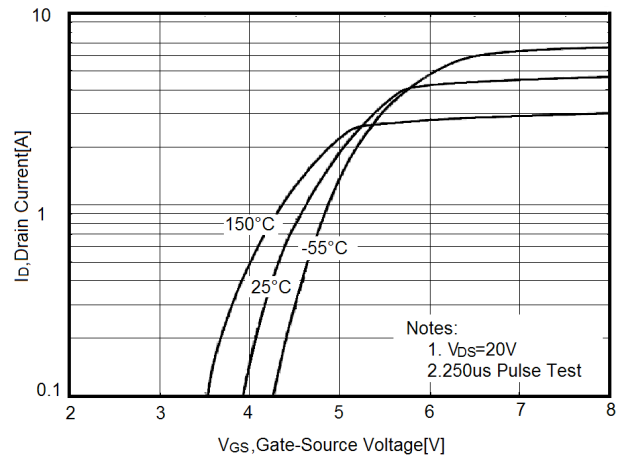


Figure5. Static drain-source on resistance

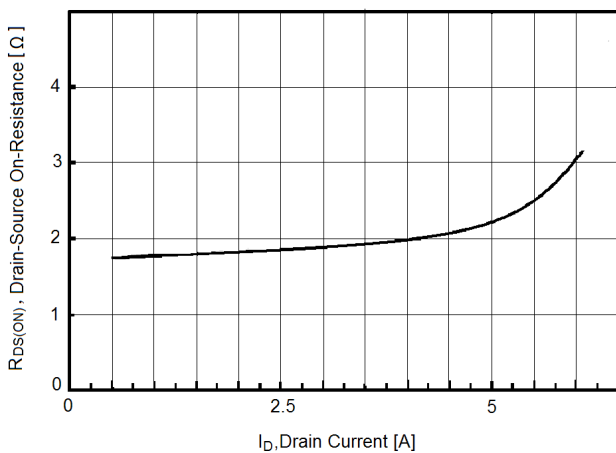


Figure6. RDS(ON) vs Junction Temperature

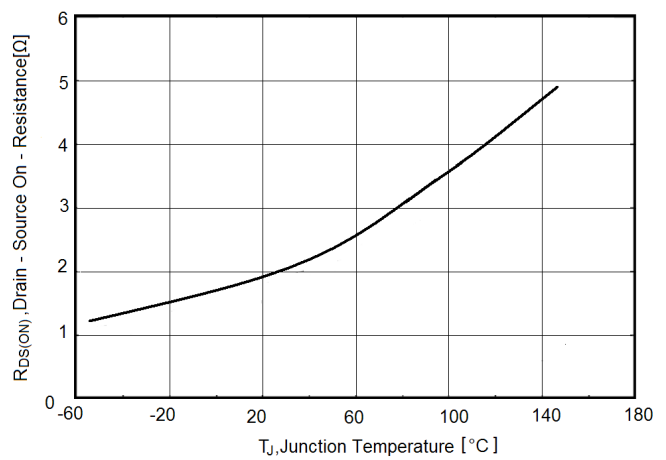




Figure7.  $BV_{DSS}$  vs Junction Temperature

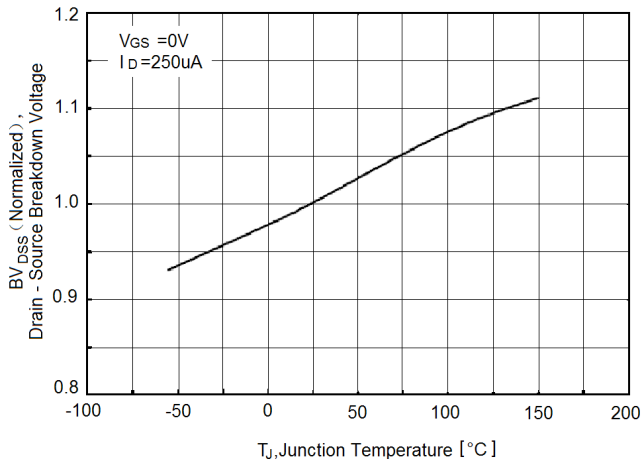


Figure8. Maximum  $I_D$  vs Junction Temperature

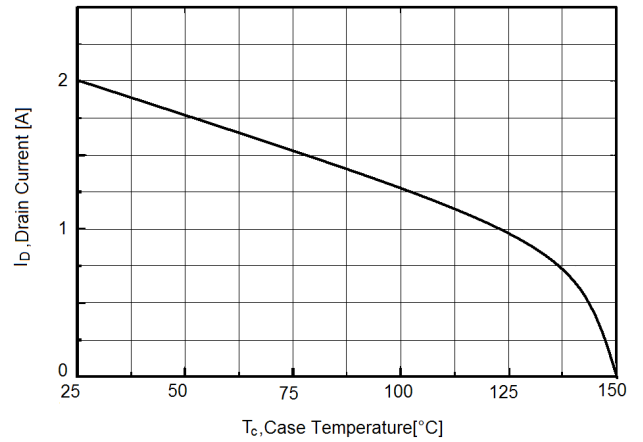


Figure9. Gate charge waveforms

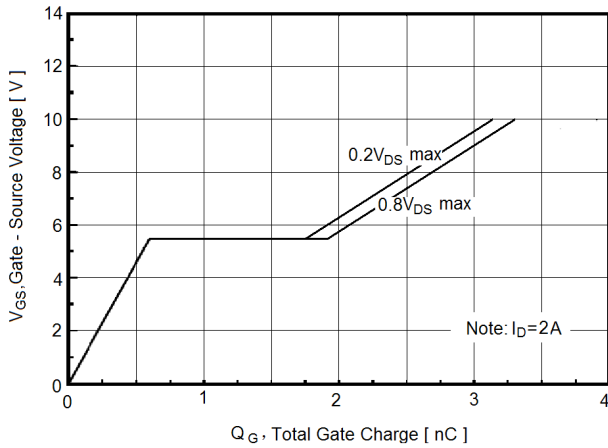


Figure10. Capacitance

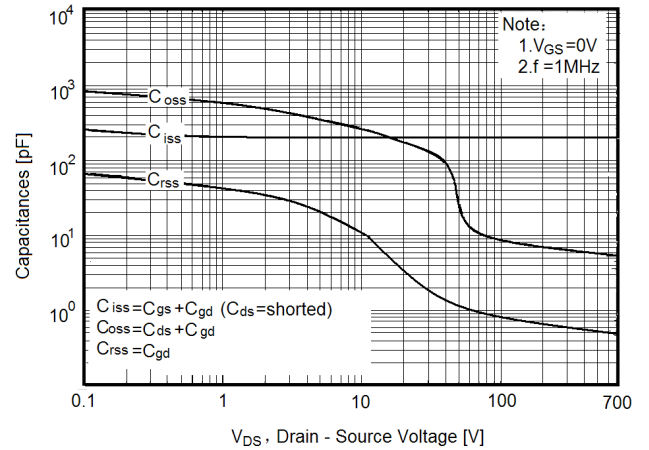
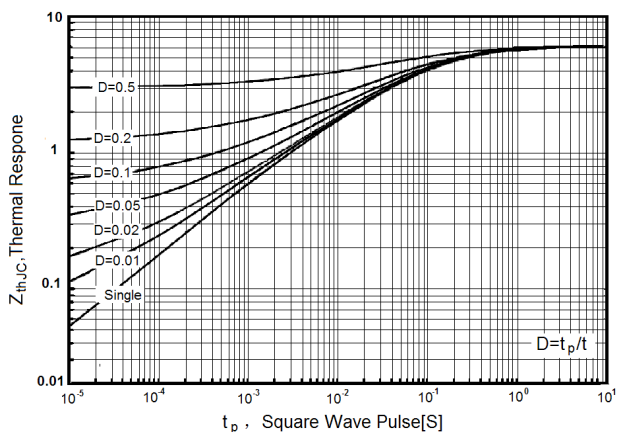
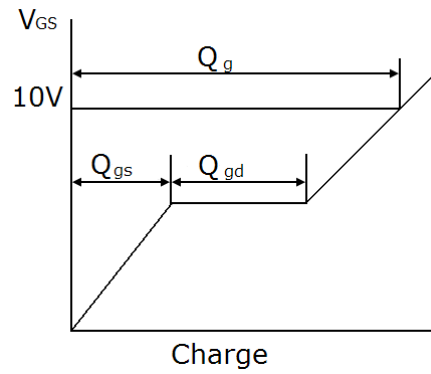
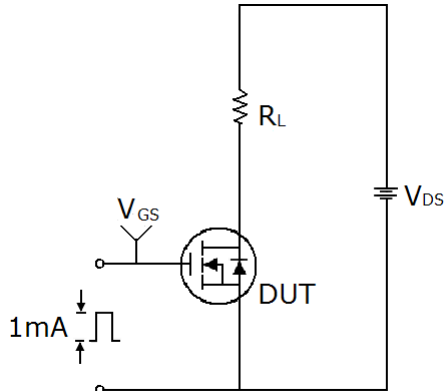


Figure11. Transient Thermal Impedance

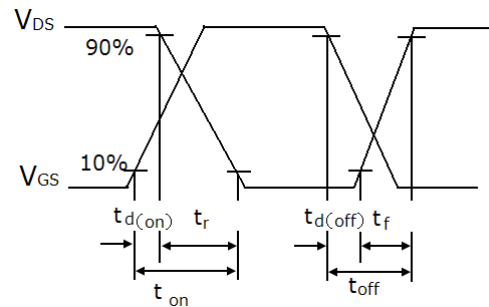
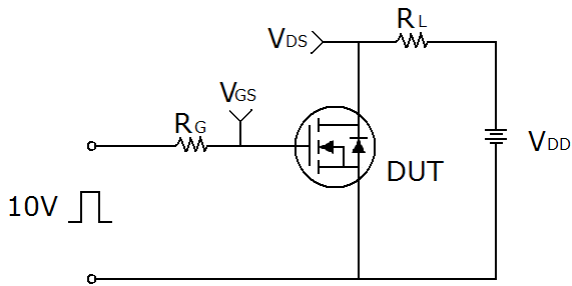


## Test circuit

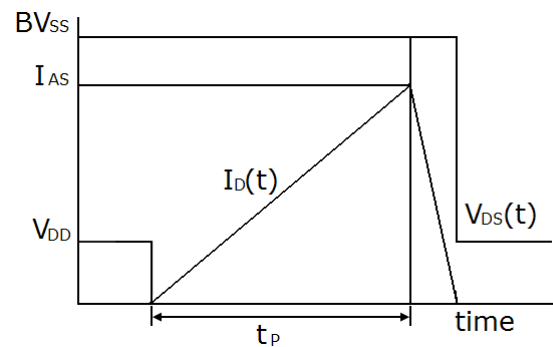
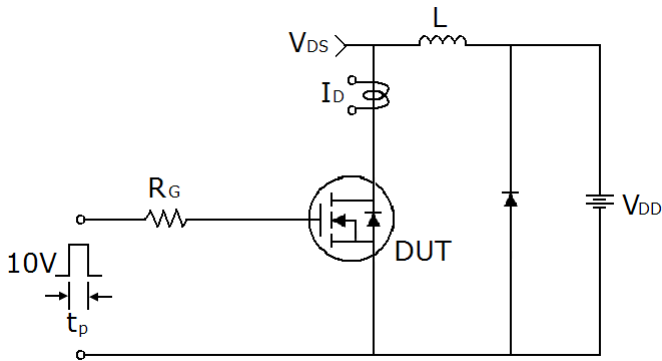
### 1) Gate charge test circuit & Waveform



### 2) Switch Time Test Circuit:

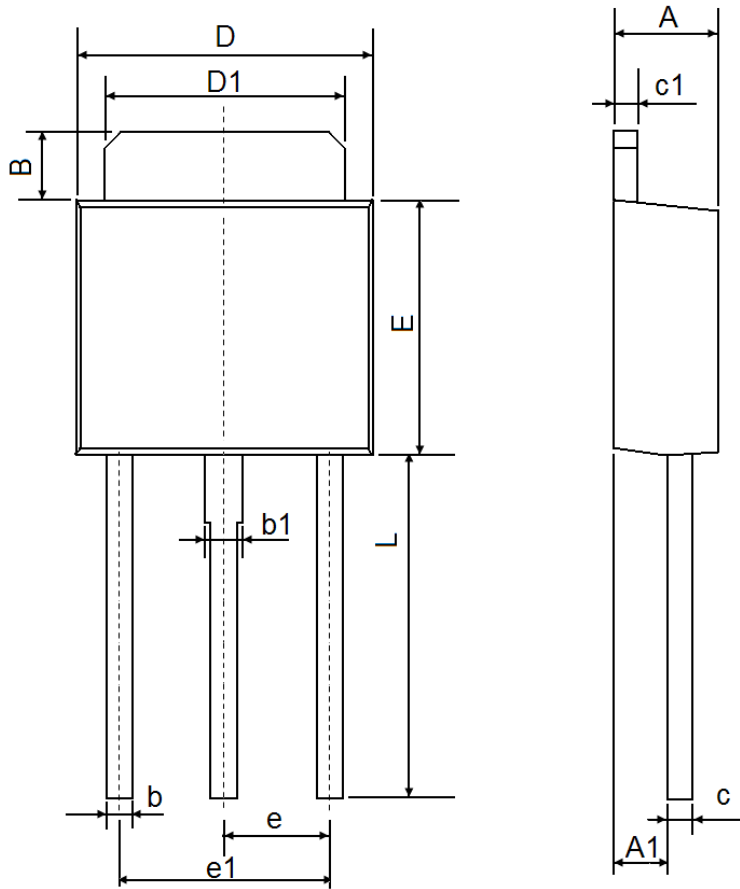


### 3) Unclamped Inductive Switching Test Circuit & Waveforms



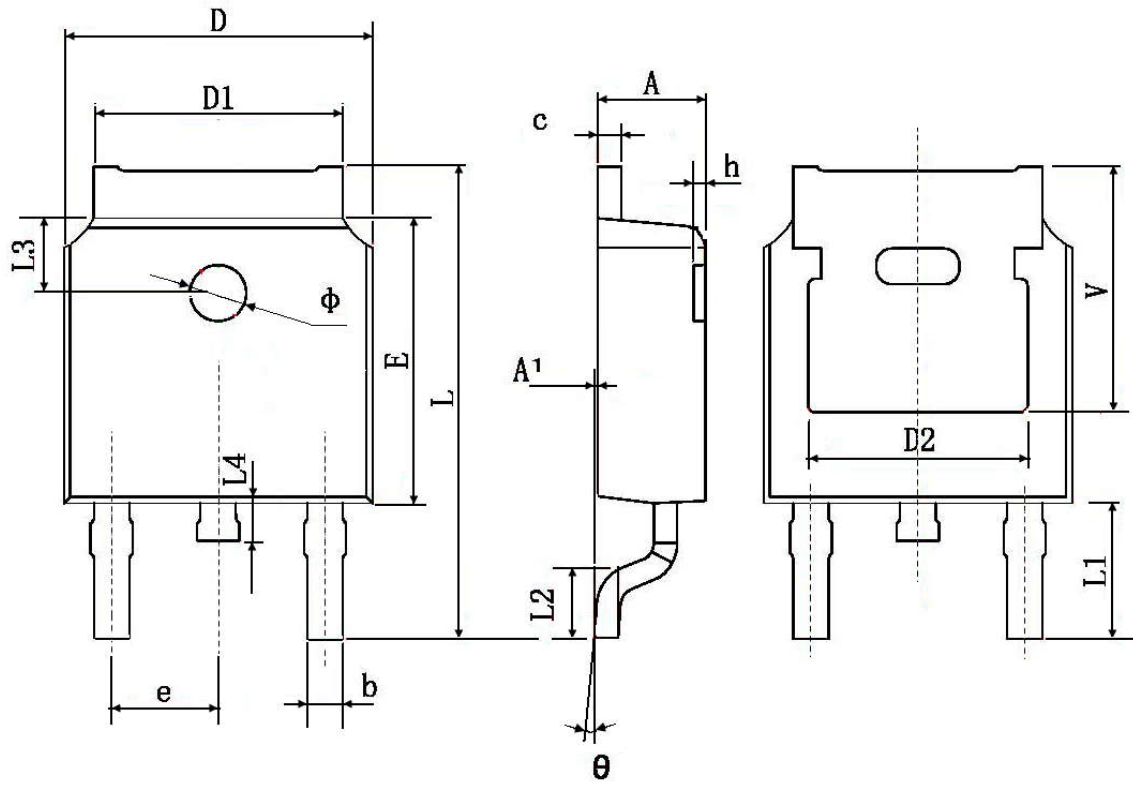


## TO-251 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	1.050	1.350	0.042	0.054
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP		0.091 TYP	
e1	4.500	4.700	0.177	0.185
L	7.500	7.900	0.295	0.311

### TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	